Graphene-based magnetic heterostructures for spintronic devices

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Young Research Leaders Group Workshop | 2024

Spintronic devices



Injection

Transport

Detection

spin relaxation length $\sim 30 \; \mu m$

M. Drögeler, et al. Nano letters 16. 3533 (2016)

Tailoring graphene band structure



3

Proximity effect



J.F. Sierra, et al. Nat. Nano. 16.8 (2021)

Proximity-induced magnetism in graphene



Proximity-induced magnetism



TS Ghiasi, et al. Nat. Nano. 16, 788 (2021)

Spin-injection by magnetic graphene



Spin-dependent Seebeck effect



Electrical and thermal generation of spin currents by the magnetic graphene

TS Ghiasi, et al. Nat. Nano. 16, 788 (2021)

Anomalous Hall effect



TS Ghiasi, et al. Nat. Nano. 16, 788 (2021)

Quantum anomalous Hall effect?





Z. Qiao, et al. *PRB*, 82. 161414 (2010) Y. Yang, Y., et al. *PRL*, *107*. 066602 (2011)

2D magnet: CrPS₄ (CPS)





10 um

Magnetic behavior of CrPS₄



12

Magnetic behavior of CrPS₄



Magnetic behavior of CrPS₄



Spin-flop detection by graphene!



Spin-flop detection by graphene!...through the anomalous Hall effect $R_{AHE} \propto M_z$



С

Anomalous Hall effect in magnetized graphene

 $(R_{AHE} \propto M_z)$



Anomalous Hall effect in magnetized graphene





90° canted \vec{M} : 700 Ω AHE

W Zhu, et al. "Interface-enhanced room-temperature Curie temperature in CrPS4/graphene van der Waals heterostructure." *PRB* 108, L100406 (2023).

T Ghiasi, et al. arXiv:2312.07515 (2023)







T Ghiasi, et al. arXiv:2312.07515 (2023)



T Ghiasi, et al. arXiv:2312.07515 (2023)

M Onodera, et al. *Nano Lett.* 19, 7282 (2019)



 $E_N = \sqrt{\alpha |N_{\rm LL}| B_{\rm T}}$ N: LL number $E^2 \propto n \propto V_{tg} \propto B_{\rm T}$ $B_{\rm T} = B_{\rm Z} + B_{\rm ps}$

Houmes, et al., "Highly Anisotropic Mechanical Response of the Van der Waals Magnet CrPS₄" *Adv. Funct. Mater.* 34.3 (2024): 2310206. *15* (2023)





Chiral states



Chiral states vs. helical states





Spin-polarized (helical) quantum Hall states

T Ghiasi, et al. arXiv:2312.07515 (2023)

Quantum anomalous spin Hall effect



Spin-polarized (helical) quantum Hall states

T Ghiasi, et al. arXiv:2312.07515 (2023)

Quantum anomalous spin Hall effect $B_z = 0$ $R_{2t} = \frac{h}{e^2} \left(\frac{1}{N_L} + \frac{1}{N_R} \right)^{-1}$



T Ghiasi, et al. arXiv:2312.07515 (2023)

Quantum anomalous spin Hall effect



Spin-polarized (helical) quantum Hall states

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Quantum anomalous spin Hall effect





Graphene-based magnetic heterostructures for spintronic devices

Spin-dependent ٠ Seebeck effect

Quantum Hall regime Anomalous Hall effect 9.00 Halphale Rose 0.6 0 ΔR_{xy} (Ω) 6.25 6 0.4 40 4.00 G (e²/h) 2 (kΩ) 0.2 $B_{z}(T)$ -1 0 B_z (T) R_{xy} (kΩ) 00 2.25 0 -2 1.00 -0.2 -4 Trace 0.25 -6 -0.4 Retrace -8 -20 -10 0 10 20 30 0 0.0 0.5 1.0 1.5 -1.5 -1.0 -0.5 B_7 (T) $V_{\rm tg}$ (V) 0.8 B_z (T) 0.2 **•** -9 18 9 🕴 0.1 0.2 16 R_{AH} (kΩ) $|B_T|$ (T) 0 20 40 60 80 100 T (K) 14 -0.1 $V_{\rm tg} = 0 \,\rm V$ T = 300 K12 $= R - B^{(8to9T)}/ne$ -0.2 10 -9 9 -6 6 -7 -4 -3 -2 0 1 2 -6 -5 -1 В_z (Т)

 N_{LL}

Helical states at B = 03

bulk

edge

٠

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Graphene-based magnetic heterostructures for spintronic devices

• Spin-dependent Seebeck effect

Quantum Hall regime Anomalous Hall effect ٠ 9.00 Hold have the 0.6 0 6.25 6 ΔR_{xy} (Ω) 3 0.4 -40 4.00 ρ_{xx} (kΩ) G (e²/h) 2 0.2 B_{z} (T) о В_z (Т) -1 2.25 R_{xy} (kΩ) 00 0 -2 1.00 -4 -0.2 1 0.25 -6 Trace -0.4 Retrace -8 0 -10 -30 -20 0 10 20 30 0.0 0.5 1.0 1.5 -1.5 -1.0 -0.5 $V_{\rm tg}$ (V) B_7 (T) • 0.8 B_z (T) 0.2 **•** -9 18 9 🕴 0.1 0.2 16 R_{AH} (kΩ) $|B_T|$ (T) σ_{xy} (e²/h) 0 20 40 60 80 100 T (K) 14 -0.1 $V_{\rm tg} = 0 \,\rm V$ T = 300 K12 $..= R - B^{(8to9T)}/ne$ -0.2 10 -9 9 -6 6 -7 -4 -3 -2 0 1 2 -6 -5 -1 В_z (Т)

NLL

Helical states at B = 0bulk edge 12 14 16 18 $V_{\rm tg}$ (V) **RT QH conductance** Device B $B_{7} = 9 T$ T = 2 K

